

REMARKS

Claim 62 and 63 are amended. Claims 62-67 are pending in the application.

Claims 62-67 stand rejected under 35 U.S.C. § 103(a) as being unpatentable over Yu, U.S. Patent No. 6,180,468 in view of Shenai, U.S. Patent No. 4,985,740. The Examiner is reminded by direction to MPEP § 2143 that a proper obviousness rejection has the following three requirements: 1) there must be some suggestion or motivation to modify or combine reference teachings; 2) there must be a reasonable expectation of success; and 3) the combined references must teach or suggest all of the claim limitations. Claim 62-67 are allowable over the combination of Yu and Shenai for at least the reason that the references, individually or in combination, fail to disclose or suggest each and every element in any of those claims.

As amended, independent claim 62 recites forming a layer of dielectric material over a substrate and patterning the dielectric material utilizing photolithographic processing to form patterned blocks separated by a gap, where each block has a sidewall within the gap formed during the photolithographic processing. Claim 62 additionally recites forming spacers along the sidewalls and implanting at least one dopant into the semiconductive material while the spacers remain along the sidewalls. The amendment to claim 62 is supported by the specification at, for example, Fig. 26 and paragraph 113. Yu discloses removal of a polysilicon gate 24 to produce a void and formation of nitride spacers 32 and 34 within the void (col. 3, lines 25-34). Yu does not disclose or suggest the claim 62 recited forming a layer of dielectric material and patterning the material utilizing photolithographic processing to form patterned blocks separated by a gap with each block having a sidewall formed during the photolithographic processing, and forming a pair of spacers along the sidewalls. Accordingly, claim 62 is not rendered obvious by Yu.

As indicated by the examiner at page 3 of the present Action, Shenai is relied upon as disclosing depositing metal over polysilicon. However, nothing in the Shenai disclosure contributes toward suggesting the claim 62 recited formation of a layer of dielectric material and patterning the dielectric material utilizing photolithographic processing to form at least two patterned blocks separated by a gap with each block having a sidewall formed during the photolithographic processing, and forming a pair of spacers along the sidewalls. Accordingly, independent claim 62 is not rendered obvious by the combination of Yu and Shenai and is allowable over this reference.

Dependent claim 63 is amended to recite conformally depositing a layer of polysilicon over the semiconductive material within the gap and along the sidewalls. The amendment to claim 63 is supported by the specification at, for example, paragraph 114 and Fig. 27. Claim 63 is allowable for at least the reasons that it depends from allowable base claim 62 and the cited combination of references do not disclose or suggest the recited conformal deposition of polysilicon over a semiconductive material within a gap and along sidewalls.

Dependent claims 64-67 are allowable over the combination of Yu and Shenai for at least the reason that they depend from allowable base claim 62.

For the reasons discussed above, claims 62-67 are allowable. Accordingly, applicant respectfully requests formal allowance in the Examiner's next Action.

Respectfully submitted,

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